



US009377692B2

(12) **United States Patent**
Xie et al.

(10) **Patent No.:** **US 9,377,692 B2**
(45) **Date of Patent:** **Jun. 28, 2016**

(54) **ELECTRIC/MAGNETIC FIELD GUIDED ACID DIFFUSION**

2005/0087701 A1* 4/2005 Lammer-Pachlinger B82Y 10/00 250/492.22

(71) Applicant: **Applied Materials, Inc.**, Santa Clara, CA (US)

2007/0000613 A1 1/2007 Pau et al.
2010/0276606 A1* 11/2010 Baars B82Y 10/00 250/396 R

(72) Inventors: **Peng Xie**, Sunnyvale, CA (US); **Ludovic Godet**, Boston, MA (US); **Tristan Ma**, Lexington, MA (US); **Joseph C. Olson**, Beverly, MA (US); **Christopher Bencher**, Cupertino, CA (US)

2011/0165515 A1 7/2011 Wang et al.
2012/0103939 A1 5/2012 Wu et al.
2012/0322011 A1 12/2012 Wu et al.
2014/0035100 A1 2/2014 Cho

FOREIGN PATENT DOCUMENTS

(73) Assignee: **APPLIED MATERIALS, INC.**, Santa Clara, CA (US)

JP 2011-103645 A 5/2011
KR 10-2012-0135701 12/2012

OTHER PUBLICATIONS

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

International Search Report and Written Opinion for Application No. PCT/US2015/030396.

(21) Appl. No.: **14/301,184**

Poppe, et al.; Improved Performance of Apex-E Photoresist with the Application of the Electric-Field Enhanced PEB; Electronics Research Laboratory; University of California; date unknown; 6 total pages.

(22) Filed: **Jun. 10, 2014**

* cited by examiner

(65) **Prior Publication Data**

US 2015/0355549 A1 Dec. 10, 2015

Primary Examiner — John C Ingham

(51) **Int. Cl.**

G03F 7/20 (2006.01)
G03F 7/38 (2006.01)
B82Y 10/00 (2011.01)

(74) *Attorney, Agent, or Firm* — Patterson & Sheridan, LLP

(52) **U.S. Cl.**

CPC . **G03F 7/38** (2013.01); **B82Y 10/00** (2013.01); **G03F 7/20** (2013.01); **G03F 7/70** (2013.01)

(57) **ABSTRACT**

(58) **Field of Classification Search**

CPC B81C 1/00119; G03F 7/20; G03F 7/2041; G03F 7/3007

Methods and apparatuses for minimizing line edge/width roughness in lines formed by photolithography are provided. The random diffusion of acid generated by a photoacid generator during a lithography process contributes to line edge/width roughness. Methods disclosed herein apply an electric field and/or a magnetic field during photolithography processes. The field application controls the diffusion of the acids generated by the photoacid generator along the line and spacing direction, preventing the line edge/width roughness that results from random diffusion. Apparatuses for carrying out the aforementioned methods are also disclosed herein.

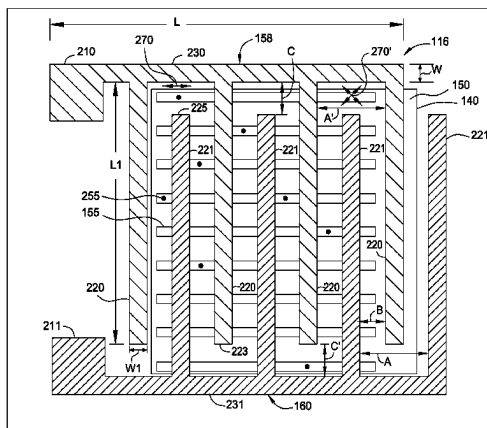
See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

7,374,867 B2 5/2008 Bristol et al.
2003/0008246 A1 1/2003 Cheng et al.

12 Claims, 4 Drawing Sheets



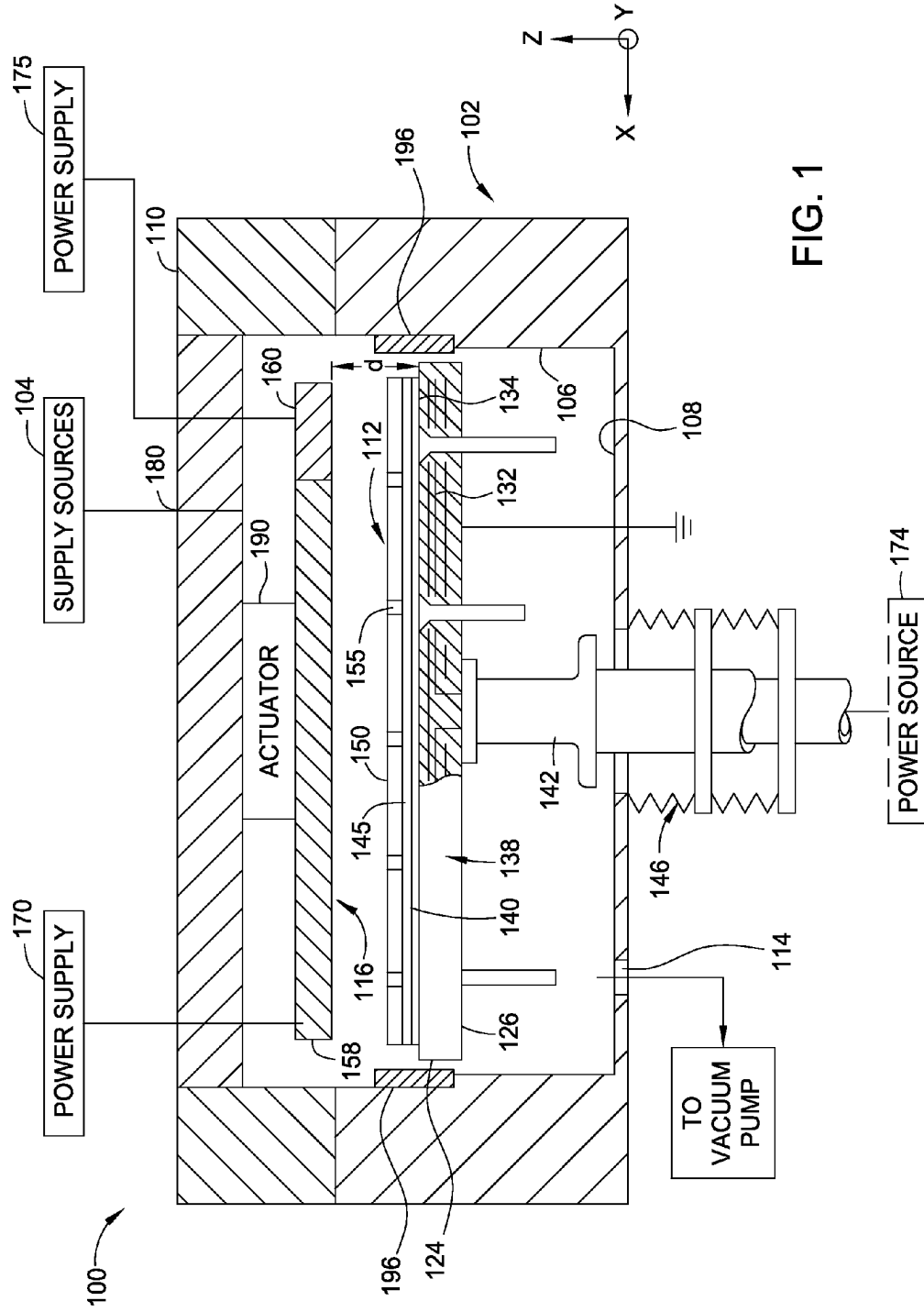


FIG. 1

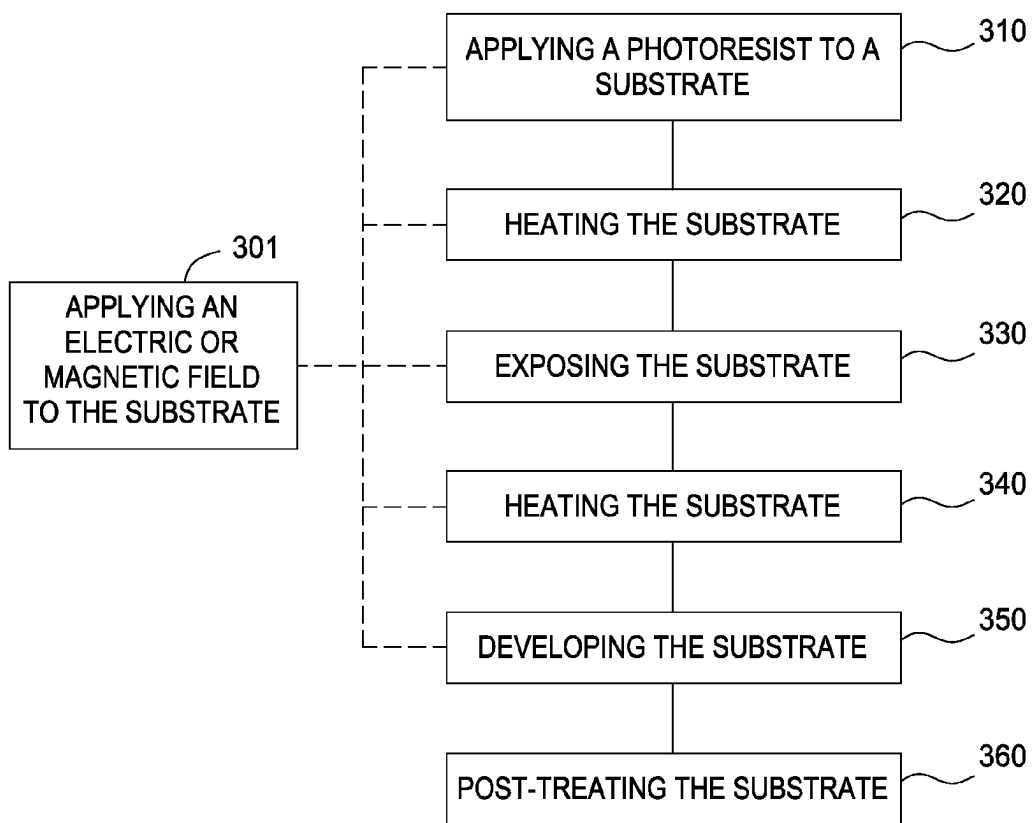


FIG. 3

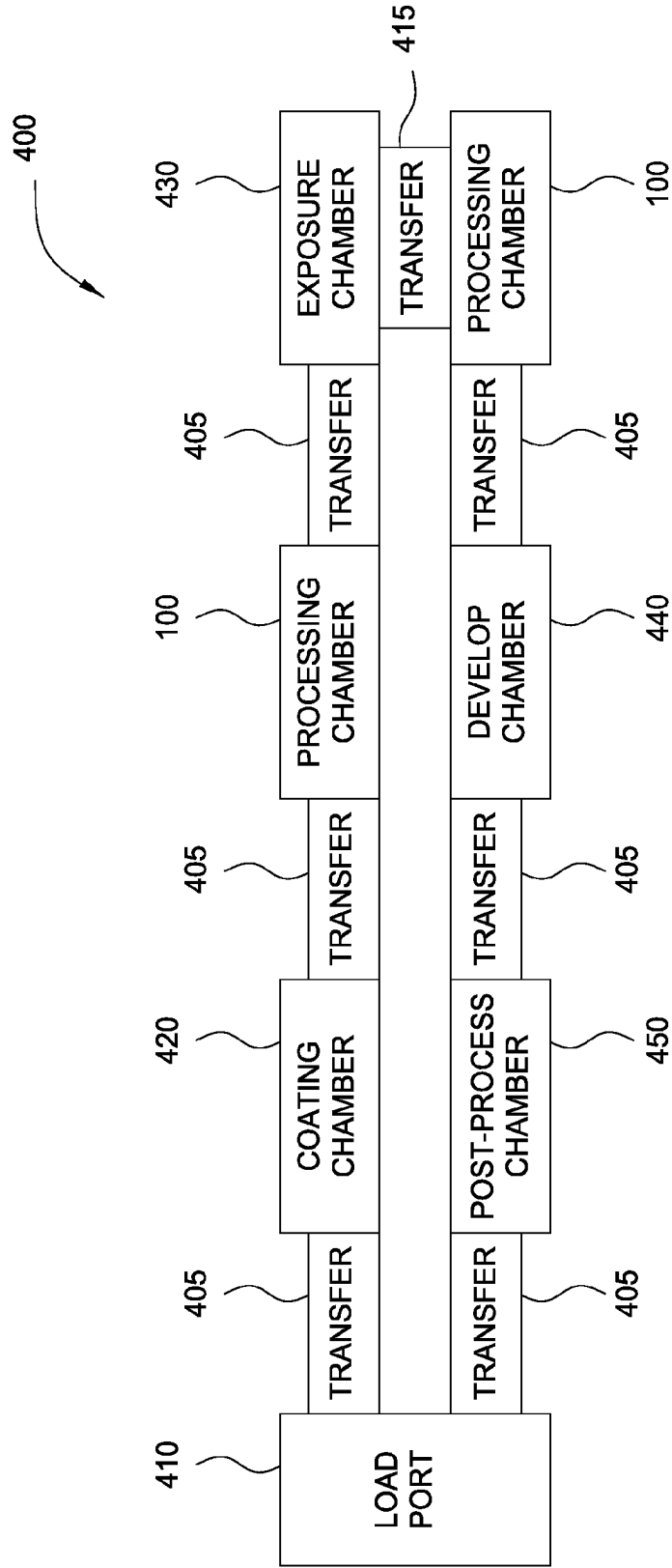


FIG. 4

ELECTRIC/MAGNETIC FIELD GUIDED ACID DIFFUSION

BACKGROUND

1. Field

The present disclosure generally relates to methods and apparatuses for processing a substrate, and more specifically to methods and apparatuses for controlling photoresist line edge/width roughness.

2. Description of the Related Art

Integrated circuits have evolved into complex devices that can include millions of components (e.g., transistors, capacitors and resistors) on a single chip. Photolithography may be used to form components on a chip. Generally the process of photolithography involves a few basic stages. Initially, a photoresist layer is formed on a substrate. The photoresist layer may be formed by, for example, spin-coating. A chemically amplified photoresist may include a resist resin and a photoacid generator. The photoacid generator, upon exposure to electromagnetic radiation in the subsequent exposure stage, alters the solubility of the photoresist in the development process. The electromagnetic radiation may have any suitable wavelength, such as a wavelength in the extreme ultra violet region. The electromagnetic radiation may be from any suitable source, such as, for example, a 193 nm ArF laser, an electron beam, an ion beam, or other source. Excess solvent may then be removed in a pre-exposure bake process.

In an exposure stage, a photomask or reticle may be used to selectively expose certain regions of the substrate to electromagnetic radiation. Other exposure methods may be maskless exposure methods. Exposure to light may decompose the photo acid generator, which generates acid and results in a latent acid image in the resist resin. After exposure, the substrate may be heated in a post-exposure bake process. During the post-exposure bake process, the acid generated by the photoacid generator reacts with the resist resin, changing the solubility of the resist during the subsequent development process.

After the post-exposure bake, the substrate, and, particularly, the photoresist layer may be developed and rinsed. Depending on the type of photoresist used, regions of the substrate that were exposed to electromagnetic radiation may either be resistant to removal or more prone to removal. After development and rinsing, the pattern of the mask is transferred to the substrate.

The evolution of chip design continually requires faster circuitry and greater circuit density. The demands for greater circuit density necessitate a reduction in the dimensions of the integrated circuit components. As the dimensions of the integrated circuit components are reduced, more elements are required to be placed in a given area on a semiconductor integrated circuit. Accordingly, the lithography process must transfer even smaller features onto a substrate, and lithography must do so precisely, accurately, and without damage. In order to precisely and accurately transfer features onto a substrate, high resolution lithography may use a light source that provides radiation at small wavelengths. Small wavelengths help to reduce the minimum printable size on a substrate or wafer. However, at such small dimensions, the roughness of the edges of a photoresist layer has become harder to control.

Therefore, there is a need for a method and an apparatus to control and minimize line edge/width roughness.

SUMMARY

In one embodiment, an apparatus for processing a substrate is provided. The apparatus includes a substrate support. The

substrate support includes a surface configured to support a substrate. The apparatus also includes a heat source configured to heat a substrate positioned on the substrate support. The apparatus also includes an electrode assembly. The electrode assembly includes at least a first electrode and a second electrode. The electrode assembly is configured to generate an electric field in a direction substantially parallel to the surface of the substrate support.

In another embodiment, an apparatus for processing a substrate is provided. The apparatus includes a processing chamber. The apparatus also includes a substrate support positioned within the vacuum processing chamber. The substrate support includes a surface. The surface is configured to support a substrate. The apparatus also includes a heat source. The heat source is configured to heat a substrate positioned on the substrate support. The apparatus further includes an electrode assembly. The electrode assembly includes a first electrode and a second electrode. The electrode assembly is configured to generate an electric field in a direction substantially parallel to the surface of the substrate support. The first electrode includes a support structure having one or more antennas projecting therefrom. Each antenna of the first electrode is substantially parallel to each other antenna of the first electrode. The second electrode also includes a support structure having one or more antennas projecting therefrom. Each antenna of the second electrode is substantially parallel to each other antenna of the second electrode. Furthermore, each antenna of the first electrode is substantially parallel to each antenna of the second electrode. Additionally, at least one antenna of the first electrode is positioned between two antennas of the second electrode, and at least one antenna of the second electrode is positioned between two antennas of the first electrode. The apparatus is configured to provide relative motion between a substrate positioned on the substrate support and the electrode assembly.

In another embodiment, a method of processing a substrate is provided. The method includes applying a photoresist layer comprising a photoacid generator to a substrate. The method also includes exposing portions of the photoresist layer to electromagnetic radiation to form substantially parallel lines of material in the photoresist layer having different chemical properties than the portions of the photoresist layer not exposed to the electromagnetic radiation. The method further includes heating the substrate after exposing the substrate to the electromagnetic radiation. The method further includes applying an electric field to the substrate in a direction parallel to the direction of the lines during the heating.

BRIEF DESCRIPTION OF THE DRAWINGS

So that the manner in which the above recited features of the present disclosure can be understood in detail, a more particular description of the disclosure, briefly summarized above, may be had by reference to embodiments, some of which are illustrated in the appended drawings. It is to be noted, however, that the appended drawings illustrate only typical embodiments of this disclosure and are therefore not to be considered limiting of its scope, for the disclosure may admit to other equally effective embodiments.

FIG. 1 is a schematic cross-sectional view of an apparatus for processing a substrate, according to one embodiment.

FIG. 2 is a top view of one embodiment of the electrode assembly and photoresist layer of FIG. 1.

FIG. 3 is a flow diagram of one method of processing a substrate.

3

FIG. 4 is a schematic of a representative processing system that may be used to process a substrate according to the embodiments disclosed herein.

To facilitate understanding, identical reference numerals have been used, wherever possible, to designate identical elements that are common to the Figures. Additionally, elements of one embodiment may be advantageously adapted for utilization in other embodiments described herein.

DETAILED DESCRIPTION

Methods and apparatuses for minimizing line edge/width roughness in lines formed by photolithography are provided. The random diffusion of acid generated by a photoacid generator during a post-exposure bake procedure contributes to line edge/width roughness. Methods disclosed herein apply an electric field and/or a magnetic field during photolithography processes. The field application controls the diffusion of the acids generated by the photoacid generator along the line and spacing direction, preventing the line edge/width roughness that results from random diffusion. Apparatuses for carrying out the aforementioned methods are also disclosed herein.

FIG. 1 is a schematic cross-sectional view of an apparatus for processing a substrate, according to one embodiment. As shown in the embodiment of FIG. 1, the apparatus may be in the form of a vacuum processing chamber 100. In other embodiments, the processing chamber 100 may not be coupled to a vacuum source.

The processing chamber 100 may be an independent processing chamber. Alternatively, the processing chamber 100 may be part of a processing system, such as, for example, an in-line processing system, a cluster processing system, or the track processing system shown in FIG. 4. FIG. 4 illustrates one representative processing system that may be used to process a substrate according to embodiments disclosed herein. As shown, a processing system 400 includes a load port 410, a coating chamber 420, a processing chamber 100, an exposure chamber 430 (such as a scanner), a second processing chamber 100, a development chamber 440, and a post-process chamber 450. As shown, each chamber of the processing system 400 is coupled to each adjacent chamber by a transfer chamber 405 or a transfer chamber 415. The transfer chambers 405 and the transfer chamber 415 may be substantially similar or different.

The load port 410 may be used to introduce or remove substrates or wafers into or out of the processing system 400. The coating chamber 420 may be used, for example, for applying a photoresist to a substrate. The coating chamber 420 may be, for example, a spin coater. The exposure chamber 430 may be used for exposing the substrate to electromagnetic energy in order to form a latent acid image in a photoresist layer on a substrate. The development chamber 440 may be used, for example, for removing portions of the photoresist layer. The post-process chamber 450 may be used, for example, to perform a variety of post-processing steps on a substrate. The processing chamber 100 is described in detail below and may be used for a pre-exposure bake, a post-exposure bake, and/or other processing steps. As described below, the processing chamber 100 includes an electrode assembly 116. However, it is to be understood that the coating chamber 420, the exposure chamber 430, and the development chamber 440 may also include an electrode assembly 116.

The processing chamber 100 includes chamber walls 102, an electrode assembly 116, and a substrate support assembly 138. The chamber walls 102 include sidewalls 106, a lid

4

assembly 110, and a bottom 108. The chamber walls 102 partially enclose a processing volume 112. The processing volume 112 is accessed through a substrate transfer port (not shown) configured to facilitate movement of a substrate 140 into and out of the processing chamber 100. In embodiments where the processing chamber 100 is part of a processing system, the substrate transfer port may allow for the substrate 140 to be transferred to and from a transfer chamber.

A pumping port 114 may optionally be disposed through one of the lid assembly 110, sidewalls 106 or bottom 108 of the processing chamber 100 to couple the processing volume 112 to an exhaust port. The exhaust port couples the pumping port 114 to various vacuum pumping components, such as a vacuum pump. The pumping components may reduce the pressure of the processing volume 112 and exhaust any gases and/or process by-products out of the processing chamber 100. The processing chamber 100 may be coupled to one or more supply sources 104 for delivering one or more source compounds into the processing volume 112.

The substrate support assembly 138 is centrally disposed within the processing chamber 100. The substrate support assembly 138 supports the substrate 140 during processing. The substrate support assembly 138 may comprise an aluminum body 124 that encapsulates at least one embedded heater 132. In some embodiments, the substrate support assembly 138 may be an electrostatic chuck. The heater 132, such as a resistive element, is disposed in the substrate support assembly 138. The heater 132 controllably heats the substrate support assembly 138 and the substrate 140 positioned thereon to a predetermined temperature. The heater 132 is configured to quickly ramp the temperature of the substrate 140 and to accurately control the temperature of the substrate 140. In some embodiments, the heater 132 is connected to and controlled by the power source 174. The power source 174 may alternatively or additionally apply power to the substrate support assembly 138. The power source 174 may be configured similarly to the power source 170, discussed below.

In some embodiments, the substrate support assembly 138 may be configured to rotate. In some embodiments, the substrate support assembly 138 is configured to rotate about the z-axis. The substrate support assembly 138 may be configured to continuously or constantly rotate, or the substrate support assembly 138 may be configured to rotate in a step manner. For example, the substrate support assembly 138 may rotate a predetermined amount, such as 90°, 180°, or 270°, and then rotation may stop for a predetermined amount of time.

In other embodiments, the processing chamber 100 may include other heating sources. For example, heat lamps may be positioned within or outside the processing chamber 100. In other embodiments, one or more lasers may be used to heat a photoresist layer 150 (or other layer) positioned on the substrate 140 and/or the antennas 220 and 221 of the electrode assembly 116. In other embodiments, the substrate support assembly 138 may be configured to circulate a high efficiency heat transfer fluid in order to more quickly increase the temperature of a substrate 140 positioned on the substrate support assembly 138.

Generally, the substrate support assembly 138 has a first surface 134 and a second surface 126. The first surface 134 is opposite the second surface 126. The first surface 134 is configured to support the substrate 140. The second surface 126 has a stem 142 coupled thereto. The substrate 140 is positioned on the first surface 134 of the substrate support assembly 138. The substrate 140 may be any type of substrate, such as a dielectric substrate, a glass substrate, a semiconductor substrate, or a conductive substrate. The substrate

140 may have a layer 145 disposed thereon. The layer 145 may be any desired layer. In other embodiments, the substrate 140 may have more than one layer 145. The substrate 140 also has a photoresist layer 150 disposed over the layer 145. The substrate 140 has been previously exposed to electromagnetic radiation in an exposure stage of a photolithography process. The photoresist layer 150 has latent image lines 155 formed therein from the exposure stage. The latent image lines 155 may be substantially parallel. In other embodiments, the latent image lines 155 may not be substantially parallel. Also as shown, the first surface 134 of the substrate support assembly 138 is separated from the electrode assembly 116 by a distance d in the z -direction. The stem 142 is coupled to a lift system (not shown) for moving the substrate support assembly 138 between an elevated processing position (as shown) and a lowered substrate transfer position. The lift system may accurately and precisely control the position of the substrate 140 in the z -direction. In some embodiments, the lift system may also be configured to move the substrate 140 in the x -direction, the y -direction, or the x -direction and the y -direction. The stem 142 additionally provides a conduit for electrical and thermocouple leads between the substrate support assembly 138 and other components of the processing chamber 100. A bellows 146 is coupled to the substrate support assembly 138 to provide a vacuum seal between the processing volume 112 and the atmosphere outside the processing chamber 100 and facilitate movement of the substrate support assembly 138 in the z -direction.

The lid assembly 110 may optionally include an inlet 180 through which gases provided by the supply sources 104 may enter the processing chamber 100. The supply sources 104 may optionally controllably pressurize the processing volume 112 with a gas, such as nitrogen, argon, helium, other gases, or combinations thereof. The gases from the supply sources 104 may create a controlled environment within the processing chamber 100. An actuator 190 may be optionally coupled between the lid assembly 110 and the electrode assembly 116. The actuator 190 is configured to move the electrode assembly 116 in one or more of the x , y , and z directions. The x and y directions are referred to herein as the lateral directions or dimensions. The actuator 190 enables the electrode assembly 116 to scan the surface of the substrate 140. The actuator 190 also enables the distance d to be adjusted. In some embodiments the electrode assembly 116 is coupled to the lid assembly 110 by a fixed stem (not shown). In other embodiments, the electrode assembly 116 may be coupled to the inside of the bottom 108 of the processing chamber 100, to the second surface 126 of the substrate support assembly 138, or to the stem 142. In still other embodiments, the electrode assembly 116 may be embedded between the first surface 134 and the second surface 126 of the substrate support assembly 138.

The electrode assembly 116 includes at least a first electrode 158 and a second electrode 160. As shown, the first electrode 158 is coupled to a power supply 170, and the second electrode 160 is coupled to an optional power supply 175. In other embodiments, one of the first electrode 158 and the second electrode 160 may be coupled to a power supply and the other electrode may be coupled to a ground. In some embodiments the first electrode 158 and the second electrode 160 are coupled to a ground and the power supply 174 delivers power to the substrate support and is a bipolar power supply that switches between a positive and negative bias. In some embodiments, the power supply 170 or the power supply 175 may be coupled to both the first electrode 158 and the second electrode 160. In other embodiments, the power supply 170 or the power supply 175 may be coupled to the first

electrode 158, the second electrode 160, and the substrate support assembly 138. In such embodiments, the pulse delay to each of the first electrode 158, the second electrode 160, and the substrate support assembly 138 may be different. The electrode assembly 116 may be configured to generate an electric field parallel to the x - y plane defined by the first surface of the substrate support assembly 138. For example, the electrode assembly 116 may be configured to generate an electric field in one of the y direction, x direction or other direction in the x - y plane.

The power supply 170 and the power supply 175 are configured to supply, for example, between about 500 V and about 100 kV to the electrode assembly 116. In some embodiments, the power supply 174 may also be configured to provide power to the electrode assembly 116. In some embodiments, any or all of the power supply 170, the power supply 174, or the power supply 175 are a pulsed direct current (DC) power supply. The pulsed DC wave may be from a half-wave rectifier or a full-wave rectifier. The power supply 170, the power supply 174, and/or the power supply 175 may be configured to provide power at a frequency of between about 10 Hz and about 1 MHz, such as about 5 kHz. The duty cycle of the pulsed DC power may be from between about 5% and about 95%, such as between about 20% and about 60%. In some embodiments, the duty cycle of the pulsed DC power may be between about 20% and about 40%. In other embodiments, the duty cycle of the pulsed DC power may be about 60%. The rise and fall time of the pulsed DC power may be between about 1 ns and about 1000 ns, such as between about 10 ns and about 500 ns. In other embodiments, the rise and fall time of the pulsed DC power may be between about 10 ns and about 100 ns. In some embodiments, the rise and fall time of the pulsed DC power may be about 500 ns. In some embodiments, any or all of the power supply 170, the power supply 174, and the power supply 175 are an alternating current power supply. In other embodiments, any or all of the power supply 170, the power supply 174, and the power supply 175 are a direct current power supply.

In some embodiments, any or all of the power supply 170, the power supply 174, and the power supply 175 may use a DC offset. The DC offset may be, for example, between about 0% and about 75% of the applied voltage, such as between about 5% and about 60% of the applied voltage. In some embodiments, the first electrode 158 and the second electrode 160 are pulsed negatively while the substrate support assembly is also pulsed negatively. In these embodiments, the first electrode 158 and the second electrode 160 are the substrate support assembly 138 are synchronized but offset. For example, the first electrode 158 may be at the "one" state while the substrate support assembly is at the "zero" state, then the substrate support assembly 138 in the one state while the first electrode 158 is at the zero state.

The electrode assembly 116 spans approximately the width of the substrate support assembly 138. In other embodiments, the width of the electrode assembly 116 may be less than that of the substrate support assembly 138. For example, the electrode assembly 116 may span between about 10% to about 80%, such as about 20% and about 40%, the width of the substrate support assembly 138. In embodiments where the electrode assembly 116 is less wide than the substrate support assembly 138, the actuator 190 may scan the electrode assembly 116 across the surface of the substrate 140 positioned on the first surface 134 of the substrate support assembly 138. For example, the actuator 190 may scan such that the electrode assembly 116 scans the entire surface of the substrate 140. In other embodiments, the actuator 190 may scan only

certain portions of the substrate **140**. Alternatively, the substrate support assembly **138** may scan underneath the electrode assembly **116**.

In some embodiments, one or more magnets **196** may be positioned in the processing chamber **100**. In the embodiment shown in FIG. 1, the magnets **196** are coupled to the inside surface of the sidewalls **106**. In other embodiments, the magnets **196** may be positioned in other locations within the processing chamber **100** or outside the processing chamber **100**. The magnets **196** may be, for example, permanent magnets or electromagnets. Representative permanent magnets include ceramic magnets and rare earth magnets. In embodiments where the magnets **196** include electromagnets, the magnets **196** may be coupled to a power source (not shown). The magnets **196** are configured to generate a magnetic field in a direction perpendicular or parallel to the direction of the electric field lines generated by the electrode assembly **116** at the first surface **134** of the substrate support assembly **138**. For example, the magnets **196** may be configured to generate a magnetic field in the x-direction when the electric field generated by the electrode assembly **116** is in the y-direction. The magnetic field drives the charged species **255** (shown in FIG. 2) and polarized species (not shown) generated by the photoacid generators in the photoresist layer **150** in a direction perpendicular to the magnetic field, such as the direction parallel with the latent image lines **155**. By driving the charged species **255** and polarized species in a direction parallel with the latent image lines **155**, line roughness may be reduced. The uniform directional movement of the charged species **255** and polarized species is shown by the double headed arrow **270** in FIG. 2. In contrast, when a magnetic field is not applied, the charged species **255** and polarized species may move randomly, as shown by the arrows **270'**.

Continuing to refer to FIG. 2, the electrode assembly **116** includes at least the first electrode **158** and the second electrode **160**. The first electrode **158** includes a first terminal **210**, a support structure **230**, and one or more antennas **220**. The second electrode **160** includes a first terminal **211**, a support structure **231**, and one or more antennas **221**. The first terminal **210**, the support structure **230**, and the one or more antennas **220** of the first electrode **158** may form a unitary body. Alternatively, the first electrode **158** may include separate portions that may be coupled together. For example, the one or more antennas **220** may be detachable from the support structure **230**. The second electrode **160** may similarly be a unitary body or be comprised of separate detachable components. The first electrode **158** and the second electrode **160** may be prepared by any suitable means. For example, the first electrode **158** and the second electrode **160** may be fabricated by machining, casting, or additive manufacturing.

The support structure **230** may be made from a conductive material, such as metal. For example, the support structure **230** may be made of silicon, polysilicon, silicon carbide, molybdenum, aluminum, copper, graphite, silver, platinum, gold, palladium, zinc, other materials, or mixtures thereof. The support structure **230** may have any desired dimensions. For example, the length **L** of the support structure **230** may be between about 25 mm and about 450 mm, for example, between about 100 mm and about 300 mm. In some embodiments, the support structure **230** has a length **L** approximately equal to a diameter of a standard semiconductor wafer. In other embodiments, the support structure **230** has a length **L** that is larger or smaller than the diameter of a standard semiconductor wafer. For example, in different representative embodiments, the length **L** of the support structure **230** may be about 25 mm, about 51 mm, about 76 mm, about 100 mm, about 150 mm, about 200 mm, about 300 mm, or about 450

mm. The width **W** of the support structure **230** may be between about 2 mm and about 25 mm. In other embodiments, the width **W** of the support structure **230** is less than about 2 mm. In other embodiments, the width **W** of the support structure **230** is greater than about 25 mm. The thickness of the support structure **230** may be between about 1 mm and about 10 mm, such as between about 2 mm and about 8 mm, such as about 5 mm. In some embodiments, the support structure **230** may be square, cylindrical, rectangular, oval, rods, or other shapes. Embodiments having round exterior surfaces may avoid arcing.

The support structure **231** may be made of the same materials as the support structure **230**. The range of dimensions suitable for the support structure **230** is also suitable for the support structure **231**. In some embodiments, the support structure **230** and the support structure **231** are made of the same material. In other embodiments, the support structure **230** and the support structure **231** are made of different materials. The lengths **L**, widths **W**, and thicknesses of the support structure **230** and the support structure **231** may be the same or different.

The one or more antennas **220** of the first electrode **158** may also be made from a conductive material. The one or more antennas **220** may be made from the same materials as the support structure **230**. The one or more antennas **220** of the first electrode **158** may have any desired dimensions. For example, a length **L1** of the one or more antennas **220** may be between about 25 mm and about 450 mm, for example, between about 100 mm and about 300 mm. In some embodiments, the one or more antennas **220** have a length **L1** approximately equal to the diameter of a standard wafer. In other embodiments, the length **L1** of the one or more antennas **220** may be between about 75% and 90% of the diameter of a standard wafer. A width **W1** of the one or more antennas **220** may be between about 2 mm and about 25 mm. In other embodiments, the width **W1** of the one or more antennas **220** is less than about 2 mm. In other embodiments, the width **W1** of the one or more antennas **220** is greater than about 25 mm. The thickness of the one or more antennas **220** may be between about 1 mm and about 10 mm, such as between about 2 mm and about 8 mm. The one or more antennas **220** may have a cross-section that is square, rectangular, oval, circular, cylindrical, or another shape. Embodiments having round exterior surfaces may avoid arcing.

Each of the antennas **220** may have the same dimensions. Alternatively, some of the one or more antennas **220** may have different dimensions than one or more of the other antennas **220**. For example, some of the one or more antennas **220** may have different lengths **L1** than one or more of the other antennas **220**. Each of the one or more antennas **220** may be made of the same material. In other embodiments, some of the antennas **220** may be made of a different material than other antennas **220**.

The antennas **221** may be made of the same range of materials as the antennas **220**. The range of dimensions suitable for the antennas **220** is also suitable for the antennas **221**. In some embodiments, the antennas **220** and the antennas **221** are made of the same material. In other embodiments, the antennas **220** and the antennas **221** are made of different materials. The lengths **L1**, widths **W1**, and thicknesses of the antennas **220** and the antennas **221** may be the same or different.

The antennas **220** may include between 1 and about 40 antennas **220**. For example, the antennas **220** may include between about 4 and about 40 antennas **220**, such as between about 10 and about 20 antennas **220**. In other embodiments, the antennas **220** may include more than 40 antennas **220**. In

some embodiments, each of the antennas 220 may be substantially parallel to the support structure 230. For example, in embodiments where the support structure 230 is straight, each antenna 220 may be substantially parallel to the support structure 230. Each of the antennas 220 may be substantially parallel to each of the other antennas 220. Each of the antennas 221 may be similarly positioned with respect to the support structure 231 and each other antenna 221.

Each of the antennas 220 may be substantially parallel to each of the antennas 221. In some embodiments, at least one of the antennas 220 is substantially parallel with at least one of the antennas 221. Each of the antennas 220 may be vertically aligned with each of the antennas 221. In some embodiments, at least one of the antennas 220 is vertically aligned with at least one of the antennas 221.

The support structure 230 and the support structure 231 are straight. In other embodiments the support structure 230 and the support structure 231 may not be straight. For example, the support structure 230 and the support structure 231 may be curved, jagged, or have other profiles or shapes. In these embodiments, each of the antennas 220 may still be substantially parallel to each of the other antennas 220. In these embodiments, each of the antennas 221 may be substantially parallel to each of the other antennas 221.

Each of the antennas 220 has a terminal end 223. Each of the antennas 221 has a terminal end 225. A distance C is defined between the support structure 230 and the terminal end 225. A distance C' is defined between the support structure 231 and the terminal end 223. Each of the distances C and C' may be between about 1 mm and about 10 mm. In other embodiments, the distances C and C' may be less than about 1 mm or greater than about 10 mm. In some embodiments, the distance C and the distance C' are equal. In other embodiments, the distance C and the distance C' are different.

A distance A is defined between facing surfaces of one of the antennas 221 and an adjacent one of the antennas 221. The distance A' is defined between facing surfaces of one antenna 220 and an adjacent one of the antennas 220. The distances A and A' may be greater than about 6 mm. For example, the distances A and A' may be between about 6 mm and about 20 mm, such as between about 10 mm and about 15 mm. The distances A and A' between each adjacent antennas 221, 220 may be the same or different. For example, the distances A' between the first and second, second and third, and third and fourth antennas of the one or more antennas 220 may be different. In other embodiments, the distances A' may be the same.

A distance B is defined between facing surfaces of one of the antennas 220 and an adjacent one of the antennas 221. The distance B may be, for example, greater than about 1 mm. For example, the distance B may be between about 2 mm and about 10 mm, such as between about 4 mm and about 6 mm. The distance B defined between may be the same, each distance B may be different, or some distances B may be the same and some distances B may be different. Modifying the distance B allows for easy control of the electric field strength.

The antennas 220, 221 may be oriented in an alternating arrangement above the photoresist layer 150. For example, the antennas 220 of the first electrode 158 and the antennas 221 of the second electrode 160 may be positioned such that at least one of the antennas 220 is positioned between two of the antennas 221. Additionally, at least one antenna 221 may be positioned between two of the antennas 220. In some embodiments, all but one of the antennas 220 is positioned between two of the antennas 221. In those embodiments, all but one of the antennas 221 may be positioned between two of

the antennas 220. In some embodiments, the antennas 220 and the antennas 221 may each have only one antenna.

In some embodiments, the first electrode 158 has a first terminal 210, and the second electrode 160 has a second terminal 211. The first terminal 210 may be a contact between the first electrode 158 and the power supply 170, the power supply 175, or a ground. The second terminal 211 may be a contact between the second electrode 160 and the power supply 170, the power supply 17, or a ground. The first terminal 210 and the second terminal 211 are shown as being at one end of the first electrode 158 and the second electrode 160, respectively. In other embodiments, the first terminal 210 and the second terminal 211 may be positioned at other locations on the first electrode 158 and the second electrode, respectively. The first terminal 210 and the second terminal 211 have different shapes and sizes than the support structure 230 and the support structure 231, respectively. In other embodiments, the first terminal 210 and the second terminal 211 may have generally the same shapes and sizes as the support structure 230 and the support structure 231, respectively.

In operation, a voltage may be supplied from a power supply, such as the power supply 170, the power supply 174, or the power supply 175, to the first terminal 210, the second terminal 211, and/or the substrate support assembly 138. The supplied voltage creates an electric field between each antenna of the one or more antennas 220 and each antenna of the one or more antennas 221. The electric field will be strongest between an antenna of the one or more antennas 220 and an adjacent antenna of the one or more antennas 221. The interleaved and aligned spatial relationship of the antennas 220, 221 produces an electric field in a direction parallel to the plane defined by the first surface 134 of the substrate assembly 138. The substrate 140 is positioned on the first surface 134 such that the latent image lines 155 are parallel to the electric field lines generated by the electrode assembly 116. Since the charged species 255 are charged, the charged species 255 are affected by the electric field. The electric field drives the charged species 255 generated by the photoacid generators in the photoresist layer 150 in the direction of the electric field. By driving the charged species 255 in a direction parallel with the latent image lines 155, line roughness may be reduced. The uniform directional movement is shown by the double headed arrow 270. In contrast, when a voltage is not applied to the first terminal 210 or the second terminal 211, an electric field is not created to drive the charged species 255 in any particular direction. As a result, the charged species 255 may move randomly, as shown by the arrows 270'.

FIG. 3 is a flow diagram of representative methods of processing a substrate 140. The method for processing the substrate 140 has multiple stages. The stages can be carried out in any order or simultaneously (except where the context excludes that possibility), and the method can include one or more other stages which are carried out before any of the defined stages, between two of the defined stages, or after all the defined stages (except where the context excludes that possibility). Not all embodiments include all the stages.

In general, the methods include a stage 310. The stage 310 includes applying a photoresist containing a photoacid generator to a substrate 140. The methods may also include a stage 320. The stage 320 includes heating the substrate 140 in a pre-exposure bake. In general, the methods also include a stage 330. The stage 330 includes exposing the substrate 140 to electromagnetic radiation. The methods may further include a stage 340. The stage 340 includes heating the substrate 140 in a post-exposure bake. The methods may also include a stage 350 and a stage 360. The stage 350 and the

11

stage 360 include developing the substrate 140 and post-treating the substrate 140, respectively.

In general, the method also includes a stage 301. The stage 301 includes applying an electric and/or a magnetic field to the substrate 140 to drive the charged species 255 generated by the photoacid generator in a direction parallel to the direction of the latent image lines 155 during the heating. The stage 301 is described herein as occurring during the stage 340. However, the stage 301 may occur during any or any combination of the other stages.

At stage 310, a photoresist is applied to the substrate 140 to form a photoresist layer 150. The photoresist layer 150 may be applied by, for example, by spin coating inside a spin coating apparatus. The substrate 140 may be introduced into and positioned on a rotatable chuck of a spin coater. Thereafter, a solution containing the photoresist may be applied to the substrate 140, and the substrate 140 may rapidly spin, resulting in a uniform photoresist layer 150.

In some embodiments, the spin coater may be part of a processing system, such as the processing system 400. In an embodiment in which the spin coater is part of the processing system 400, the spin coater may be within the coating chamber 420. In such an embodiment, the substrate 140 may enter the processing system 400 through the load port 410 and thereafter be transferred to the coating chamber 420 through a transfer chamber 405.

The spin coater may include an electrode assembly 116 coupled to one or more power sources. For example, the coating chamber 420 may include an electrode assembly 116 coupled to one or more power sources. The substrate 140 may be positioned relative to the electrode assembly 116 such that the electrode assembly 116 may produce an electric field parallel to the lateral dimensions of the substrate 140. In some embodiments, the electrode assembly 116 of the spin coater may also be coupled to an actuator 190. The spin coater may also include magnets 196. The magnets 196 may be configured to generate a magnetic field in a direction perpendicular or parallel to the direction of the electric field lines generated by the electrode assembly 116.

The photoresist may include a solvent, a photoresist resin, and a photoacid generator. The photoresist resin may be any positive photoresist resin or any negative photoresist resin. Representative photoresist resins include acrylates, Novolac resins, poly(methylmethacrylates), and poly(olefin sulfones). Other photoresist resins may also be used.

Upon exposure to electromagnetic radiation, the photoacid generator generates charged species 255, such as an acid cation and an anion. The photoacid generator may also generate polarized species. The photoacid generator sensitizes the resin to electromagnetic radiation. Representative photoacid generators include sulfonate compounds, such as, for example, sulfonated salts, sulfonated esters, and sulfonyloxy ketones. Other suitable photoacid generators include onium salts, such as aryl-diazonium salts, halonium salts, aromatic sulfonium salts and sulfoxonium salts or selenium salts. Other representative photoacid generators include nitrobenzyl esters, s-triazine derivatives, ionic iodonium sulfonates, perfluoroalkanesulfonates, aryl triflates and derivatives and analogs thereof, pyrogallol derivatives, and alkyl disulfones. Other photoacid generators may also be used.

At optional stage 320, the substrate 140 is heated in a pre-exposure bake. During the pre-exposure bake, the substrate is heated to partially evaporate the photoresist solvents. The pre-exposure bake of stage 320 and the photoresist application of stage 310 may occur in the same chamber. For example, both stages may occur in a spin coater. In one embodiment, both stages may occur in the coating chamber

12

420. Alternatively, the substrate 140 may be transferred to a different processing chamber. For example, in an embodiment using the processing system 400, the substrate 140 may be transferred from the coating chamber 420 to a processing chamber 100 through a transfer chamber 405.

As noted above, the processing chamber 100 includes an electrode assembly 116. The substrate 140 may be positioned in the processing chamber 100 relative to the electrode assembly 116 such that the electrode assembly 116 may produce an electric field parallel to the lateral dimensions of the substrate 140. In some embodiments, the electrode assembly 116 of the processing chamber 100 may also be coupled to an actuator 190. The processing chamber 100 may also include magnets 196. The magnets 196 may be configured to generate a magnetic field in a direction perpendicular or parallel to the direction of the electric field lines generated by the electrode assembly 116.

At stage 330, the substrate 140 and portions of the photoresist layer 150 are exposed to electromagnetic radiation. Stage 330 may be performed in an exposure chamber. In one embodiment, after the completion of stage 320, the substrate 140 is transferred to an exposure chamber. In an embodiment using the processing system 400, the substrate 140 may be transferred from the processing chamber 100 to the exposure chamber 430 through the transfer chamber 405. The exposure chamber may also include an electrode assembly 116 coupled to one or more power sources and/or an actuator 190 and magnets 196. The substrate 140 may be positioned in the exposure chamber relative to the electrode assembly 116 and magnets 196 as described in relation to the coating chamber 420.

In stage 330, portions of the photoresist layer 150 are selectively exposed and portions of the photoresist layer 150 are selectively unexposed. Portions of the photoresist layer 150 exposed to electromagnetic radiation may have different chemical properties than the portions of the photoresist layer 150 not exposed to the electromagnetic radiation. The acid generated by the photoacid generator results in a latent acid image in the resist resin. In some embodiments, a photomask or reticle may be positioned between the photoresist layer 150, and the photoresist layer 150 may be exposed to electromagnetic radiation through the mask or reticle. The mask or reticle may be configured to transfer a pattern containing lines to the photoresist layer 150. In other embodiments, a pattern containing lines may be transferred to the photoresist layer 150 using maskless lithography techniques. The transferred latent image lines 155 may have any desired length, width, and spacing between latent image lines 155. For example, in some embodiments, the line widths and line spacings may be between about 10 nm and about 16 nm. In other embodiments the line widths and spacings may be less than about 10 nm or greater than about 16 nm. In some embodiments, the length of the latent image line 155 is about 150% of the width of the latent image line 155. In other embodiments, the length of the latent image line 155 is greater than about 200% of the width of the latent image line 155, such as for example, greater than about 1000% of the width of the latent image line 155.

The electromagnetic radiation generally has a wavelength suitable for exposing the photoresist layer 150. For example, the electromagnetic radiation may have a wavelength in the extreme ultra violet (EUV) range, such as between about 10 nm and about 124 nm. In other embodiments, the electromagnetic radiation may be generated by an argon fluoride laser. In such an embodiment, the electromagnetic radiation may have a wavelength of about 193 nm. In some embodiments, the wavelength may be 248 nm. Other embodiments may use

different wavelengths. In some embodiments, the electromagnetic radiation is from an electron beam or an ion beam.

At stage 340, the substrate 140 is heated in a post-exposure bake process. In one embodiment, after the completion of stage 330, the substrate 140 is transferred to a processing chamber. In some embodiments, the processing chamber may be the processing chamber 100. In embodiments using the processing system 400, the substrate 140 may be transferred from the exposure chamber 430 to the processing chamber 100 through the transfer chamber 415. The substrate 140 may be positioned on the first surface 134 of the substrate support assembly 138. The power source 174 may provide power to the embedded heater 132 to heat the substrate 140. The embedded heater 132 may quickly heat the substrate 140 and the photoresist layer 150. For example, the embedded heater 132 may raise the temperature of the photoresist layer 150 from ambient temperature to between about 70° C. and about 160° C., such as between about 90° C. and 140° C., in less than about 2 seconds. The temperature of the substrate 140 and the photoresist layer 150 may be maintained at between about 70° C. and about 160° C., such as between about 90° C. and 140° C., during stage 340. In other embodiments, the substrate 140 may be heated by a resistive heater, a heat lamp, a laser, or other heat source. In still other embodiments, the substrate 140 may be heated by more than one of the embedded heater 132, the resistive heater, the heat lamp, the laser, and the other heat sources. In some embodiments, the power supply 170 and the power supply 175 may also heat the substrate 140.

A heat lamp, laser, or other heat source may also heat the antennas 220 and the antennas 221. For example, the heat lamp, laser, or other heat source may heat the antennas 220 and the antennas 221 to between about 70° C. and about 160° C., such as between about 90° C. and 140° C., during stage 340. In some embodiments, the temperatures of the antennas 220 and the antennas 221 are controlled to substantially match the temperature of the substrate support assembly 138. Matching the temperature of the substrate support assembly 138 to the temperature of the antennas 220 and the antennas 221 allows for more uniform control of the temperature of the photoresist layer 150 during stage 340. During the post-exposure bake, photoacid generators in the photoresist layer 150 may continue to alter the chemical properties of the exposed portions of the photoresist layer 150.

Optionally during stage 340, the pressure of the processing chamber 100 may be reduced by a vacuum source. The processing volume 112 may be reduced, for example, by the vacuum pump coupled to the processing volume 112 through the pumping port 114. In some embodiments, the pressure of the processing chamber 100 may be reduced to at least 10^{-5} Torr. For example, the pressure may be reduced to between about 10^{-6} Torr and about 10^{-8} Torr. Reducing the pressure may reduce or eliminate arcing during processing. In some embodiments, the pressure of the processing chamber 100 is not reduced. By not reducing the pressure, heat from the heat sources may be more readily transferred to the substrate 140. In some embodiments, the pressure in the processing volume 112 is reduced to a pressure between ambient pressure and 10^{-5} Torr.

During stage 340, a field is applied to the photoresist layer 150 to drive the charged species 255 created by the photoacid generator in the direction of the latent image lines 155. The field may be an electric field or both an electric and a magnetic field. An electric field may be applied to the photoresist layer 150, for example, by the electrode assembly 116. In some embodiments, the electrode assembly 116 and the photoresist layer 150 remain stationary with respect to each other while

the electrode assembly 116 generates an electric field. In other embodiments, the electrode assembly 116 and the photoresist layer 150 move relative to each other while the electrode assembly 116 generates an electric field. Relative motion may, for example, allow the electric field to scan the surface of the substrate 140. As discussed below, scanning the surface of the substrate 140 with an electric field may allow for higher throughput and more precise control of the application of the electric field to the substrate 140. Scanning also allows for the application of a more uniform electric field to the substrate 140, which allows for a more uniform line edge roughness reduction.

In some embodiments, the distance d between the substrate 140 and the electrode assembly 116 may be adjusted. For example, in the embodiment shown in FIG. 1, the distance d may be adjusted by either the actuator 190 or by the lift system coupled to the substrate support assembly 138. The actuator 190 may move the electrode assembly 116 towards the substrate 140. Additionally or alternatively, the lift system coupled to the substrate support assembly 138 may move the substrate 140 towards the electrode assembly 116. In some embodiments, the distance d is between about 0.1 mm and about 100 mm. For example, the distance d may be between about 8 mm and about 14 mm. In other embodiments, the distance d is less than about 0.1 mm or greater than about 100 mm. Adjusting the distance d allows the strength of the electric field applied to the charged species 255 to be adjusted. A smaller distance d applies a stronger electric field to the charged species 255.

In embodiments where the electrode assembly 116 and the photoresist layer 150 remain stationary with respect to each other, the electrode assembly 116 may have lateral dimensions that are larger than or substantially the same as the lateral dimensions of the photoresist layer 150. In other embodiments, the lateral dimensions of the electrode assembly 116 may be smaller than the lateral dimensions of the photoresist layer 150. In one embodiment where the lateral dimensions of the electrode assembly 116 are smaller than the lateral dimensions of photoresist layer 150, the electrode assembly 116 may be positioned over a specific region of the photoresist layer 150. For example, the specific region of the photoresist layer 150 may be where at least some of the latent image lines 155 are transferred during stage 330.

The electrode assembly 116 may generate an electric field in a direction along the length of the latent image lines 155. In other words, the electrode assembly 116 may generate an electric field parallel to the latent image lines 155. The generated electric field may have a field strength of, for example, between about 0.1 MV/m and about 100 MV/m, such as, between about 0.5 MV/m and about 10 MV/m. The electric field may be generated by, for example, the power supply 170, the power supply 175, and/or the power supply 174. The power provided by the one or more power supplies may have the properties discussed above in relation to FIG. 1. The above power conditions may allow for the charged species 255 to diffuse in the direction of the latent image lines 155 on the order of between about 10 nm and about 50 nm while limiting the diffusion perpendicular to the latent image lines 155 to less than about 5 nm. In some embodiments, the diffusion in the direction of the latent image lines 155 may be less than about 10 nm or greater than about 50 nm while the perpendicular diffusion is about 5 nm. In some embodiments, the pulsed DC power conditions allow for the electric field to act on the charged species 255 long enough to move the charged species 255 between about 10 nm and about 50 nm before switching the polarity. In other embodiments, the charged species may move less than about 10 nm or more than

15

about 50 nm before switching polarity. In some embodiments, the power conditions provide a ratio of diffusion of the charged species 255 substantially along the direction of the latent image lines 155 to the diffusion of charged species 255 in a direction substantially perpendicular to the direction of the latent image lines 155 greater than about 5:1. For example, the ratio may be greater than about 10:1, such as greater than about 20:1. In some embodiments the ratio is between about 5:1 and about 20:1. In other embodiments, the ratio is between about 10:1 and about 20:1.

The power supply 170, the power supply 174, and/or the power supply 175 may continue to apply a voltage to the first terminal 210 and/or the second terminal 211 for a period of time. For example, the power supply may continue to supply the voltage for between about 30 seconds and about 180 seconds, such as between about 45 seconds and about 90 seconds, such as about 60 seconds. In other embodiments, the voltage may be applied for fewer than 30 seconds or more than 180 seconds. The length of time that the voltage is applied may depend on the photoresist layer 150 dimensions, the electrode assembly 116, the amount of photoacid generator incorporated into the photoresist layer 150, the electric field strength, and other variables. If the first terminal 210, the second terminal 211, or substrate support assembly 138 is not supplied power, the respective component may be connected to a ground.

The strength of the electric field applied to the photoresist layer 150 can be modified by varying several variables. For example, the electric field strength can be modified by the amount of voltage applied to the first terminal 210 and/or the second terminal 211. In some embodiments, the electric field strength may also be controlled by varying the distance d between the electrode assembly 116 and the photoresist layer 150. The electric field strength may also be modified by the dimensions of the electrode assembly 116. For example, the dimensions A, B, and C may affect the strength of the electric field at the photoresist layer 150.

In embodiments where the electrode assembly 116 and the photoresist layer 150 move relative to each other, the electrode assembly 116 and the photoresist layer 150 may have identical, substantially similar, or different lateral dimensions. In one embodiment, one of the lateral dimensions, such as the x-dimension, is at least substantially the same size as the x-dimension of the photoresist layer 150 and/or the substrate 140. In that embodiment, the electrode assembly 116 may have a size in another lateral dimension, such as the y-dimension, that is smaller than the y-dimension photoresist layer and/or substrate 140. In that embodiment, the relative movement between the electrode assembly 116 and the photoresist layer 150 may be such that the x-dimension of the electrode assembly 116 moves relatively along the y-dimension of the photoresist layer 150. The relative motion may result in the electrode assembly 116 scanning above the entirety or a portion of the surface of the photoresist layer 150. Scanning may allow for higher throughput and for more precise control of the application of the electric field to the photoresist layer 150. For example, in some embodiments, the pattern transferred to the photoresist layer 150 may have a first set of latent image lines 155 at a first location and a second set of latent image lines 155 at a second location. The first set of latent image lines 155 and the second set of latent image lines 155 may be oriented in different directions. Scanning may allow for an electric field to be applied to the first set of latent image lines 155 by the electrode assembly 116 such that the electric field is parallel to the first set of latent image lines 155. Thereafter, the actuator 190 may move the electrode assembly 116 to the second location and orient the

16

electrode assembly 116 so that the electric field generated by the electrode assembly is parallel to the second set of latent image lines 155.

In another embodiment where the electrode assembly 116 is smaller than the photoresist layer 150, both lateral dimensions of the electrode assembly 116 are smaller than the lateral dimensions of the photoresist layer 150. In those embodiments, the electrode assembly 116 may scan the entirety or a portion of the surface of the photoresist layer 150. In some embodiments where both lateral dimensions of the electrode assembly 116 are smaller than the lateral dimensions of the photoresist layer 150, the electrode assembly 116 may have lateral dimensions sized to be substantially similar to the lateral dimensions of die on the substrate 140. In those embodiments, the electrode assembly 116 may sequentially apply an electric field to each die or to only some of the die on the substrate 140.

In one embodiment, the actuator 190 may provide the relative motion between the photoresist layer 150 and the electrode assembly 116. In other embodiments, the substrate support assembly 138 may be configured to provide relative motion between the photoresist layer 150 and the electrode assembly 116. In still other embodiments, both the actuator 190 and a movable substrate support assembly 138 may effectuate relative motion. In other embodiments, a substrate 140 may be positioned on a conveyor system, and the conveyor system may move the substrate 140 relative to one or more electrode assemblies 116. The relative motion between the electrode assembly 116 and the photoresist layer 150 may have a velocity of between about 1 mm/sec and about 1000 mm/sec, such as between about 10 mm/sec and about 100 mm/sec, such as about 500 mm/sec. The velocity of relative motion may be adjusted to ensure that the photoresist layer 150 is exposed to the electric field for a time long enough to reduce the line edge/width roughness to the desired level. The velocity may depend on several variables, including the concentration of and identity of the photoacid generator and the composition of photoresist resin.

In some embodiments including relative motion between the electrode assembly 116 and the photoresist layer 150, the distance d (z-direction) varies over time. Varying d during scanning alters the electric field strength, thus modulating the profile of the photoresist layer 150. In other embodiments including relative motion disclosed herein, the substrate support assembly 138 rotates relative to the electrode assembly 116. For example, the substrate support assembly 138 may rotate about the z-axis. The substrate support assembly 138 may be configured to continuously or constantly rotate, or the substrate support assembly 138 may be configured to rotate in a step manner. For example, the substrate support assembly 138 may rotate a predetermined amount, such as 90°, 180°, or 270°, and then rotation may stop for a predetermined amount of time. In other embodiments, the electrode assembly 116 rotates relative to the substrate support assembly 138. The electrode assembly 116 may rotate in the same manner as the substrate support assembly 138.

In embodiments including relative motion, the electric field may also be generated by any or all of the power supply 170, the power supply 174, and the power supply 175. The properties of the applied voltage and power may be the same in embodiments including relative motion as in embodiments involving no relative movement. In scanning embodiments, the power may be applied for between about 30 seconds and about 360 seconds, such as between about 45 seconds and about 180 seconds, such as about 90 seconds. The length of time that the voltage is applied may depend on the photoresist layer 150 dimensions, the electrode assembly 116, the

amount of photoacid generator incorporated into the photoresist, the electric field strength, the rate of relative motion, and other variables. In embodiments including relative motion between the substrate **140** and the electrode assembly **116**, the relative motion may occur only while an electric field is applied, only while an electric field is not applied, or both while an electric field is applied and while an electric field is not applied. For example, in embodiments where the relative motion is caused by the rotation of the substrate support assembly **138**, the electric field may be applied during the rotation, the electric field may not be applied during the rotation, or the electric field may be applied both while the substrate support assembly **138** is rotating and not rotating.

In some embodiments, a magnetic field is generated in order to drive the charged species **255** in the direction of the latent image lines **155**. Magnets, such as the magnets **196**, may apply a magnetic field in a direction perpendicular or parallel to the latent image lines **155**, resulting in lines having a reduced line edge/width roughness. The magnets **196** may be, for example, permanent magnets or electromagnets. In other embodiments, the magnets **196** may be positioned elsewhere in the processing chamber **100** or outside the processing chamber **100**. The magnetic field strength at the photoresist layer **150** may be between about 0.1 Tesla (T) and about 10 T, such as between about 1 T and about 5 T. In embodiments including a magnetic field, the magnets **196** may remain stationary or move relative to the photoresist layer **150** and the substrate **140**.

In some embodiments, the electrode assembly **116** generates an electric field and the magnets **196** generate a magnetic field. The electric field may be generated in the direction of the latent image lines **155** and a magnetic field may be generated in a direction perpendicular to the latent image lines **155**. In an embodiment including a magnetic field and an electric field the magnetic field may be perpendicular to the electric field.

At optional stage **350**, the photoresist is developed. In one embodiment, after the completion of stage **340**, the substrate **140** is transferred to a development chamber. In embodiments using the processing system **400**, the substrate **140** may be transferred from the processing chamber **100** to the development chamber **440** through the transfer chamber **405**. The development chamber **440** may also include an electrode assembly **116** coupled to one or more power sources and/or an actuator **190** and magnets **196**. The substrate **140** may be positioned in the development chamber **440** relative to the electrode assembly **116** and magnets **196** as described in relation to the coating chamber **420**.

In stage **350**, the photoresist layer **150** may be developed by, for example, exposing the photoresist layer **150** to a developer, such as a sodium hydroxide solution, a tetramethylammonium hydroxide solution, xylene, or Stoddard solvent. The substrate **140** may be rinsed with, for example, water or n-butylacetate. By stage **350**, the latent image lines **155** may no longer be latent. The lines **155** on the substrate **140** will have less line edge/width roughness compared to conventional techniques.

At optional stage **360**, additional post-processing steps may be performed. The additional post-processing steps may be performed, for example, in a post-processing chamber. In an embodiment using the processing system **400**, the substrate **140** may be transferred from the development chamber **440** through the transfer chamber **405** to the post-processing chamber **450** for post-processing. For example, after rinsing, the substrate **140** may be hard baked and inspected. After inspection, an etching process may be performed on the sub-

strate **140**. The etching process uses the features of photoresist layer **150**, such as the lines **155**, to transfer a pattern to the layer **145**.

The previously described embodiments have many advantages, including the following. For example, the embodiments disclosed herein may reduce or eliminate line edge/width roughness. Additionally, the embodiments disclosed herein may allow for new fabrication process flows. The aforementioned advantages are illustrative and not limiting. It is not necessary for all embodiments to have all the advantages.

While the foregoing is directed to embodiments of the present disclosure, other and further embodiments of the disclosure may be devised without departing from the basic scope thereof, and the scope thereof is determined by the claims that follow.

What is claimed is:

1. An apparatus for processing a substrate, the apparatus comprising:

a substrate support, the substrate support comprising a surface configured to support a substrate thereon;
 a heat source, the heat source configured to heat a substrate positioned on the surface of the substrate support;
 an electrode assembly positioned opposite the surface of the substrate support, the electrode assembly comprising a first electrode and a second electrode, wherein:
 the first electrode comprises one or more antennas;
 the second electrode comprises one or more antennas;
 at least one antenna of the first electrode and at least one antenna of the second electrode are interleaved; and
 the electrode assembly is configured to generate an electric field in a direction substantially parallel to the surface of the substrate support; and
 a magnetic field source, wherein the magnetic field source is configured to generate a magnetic field in a direction substantially perpendicular to the electric field and parallel to the surface of the substrate support.

2. The apparatus of claim 1:

wherein the one or more antennas of the first electrode project from a first support structure, and wherein each antenna of the first electrode is substantially parallel to each other antenna of the first electrode;
 wherein the one or more antennas of the second electrode project from a second support structure, and wherein each antenna of the second electrode is substantially parallel to each other antenna of the second electrode; and
 wherein each antenna of the first electrode is substantially parallel to each antenna of the second electrode.

3. The apparatus of claim 2, wherein the distance between each adjacent antenna of the first electrode is substantially the same, the distance between each adjacent antenna of the second electrode is substantially the same, and the distance between each adjacent antenna of the first electrode and each adjacent antenna of the second electrode is substantially the same.

4. The apparatus of claim 3, wherein the first electrode and the second electrode each have between about 4 and about 40 antennas.

5. The apparatus of claim 4, wherein the apparatus is configured to provide relative motion between a substrate positioned on the substrate support and the electrode assembly.

6. The apparatus of claim 4, wherein the substrate support and electrode assembly are positioned within a vacuum chamber.

19

7. The apparatus of claim 1, wherein the magnetic field source provides a magnetic field strength of between about 0.1 T and about 10 T above the surface of the substrate support.

8. The apparatus of claim 1, wherein:

the one or more antennas of the first electrode project from a first support structure, and wherein each antenna of the first electrode is substantially parallel to each other antenna of the first electrode;

the one or more antennas of the second electrode project from a second support structure, and wherein each antenna of the second electrode is substantially parallel to each other antenna of the second electrode;

each antenna of the first electrode is substantially parallel to each antenna of the second electrode;

the distance between each adjacent antenna of the first electrode is substantially the same, the distance between each adjacent antenna of the second electrode is substantially the same, and the distance between each adjacent antenna of the first electrode and each adjacent antenna of the second electrode is substantially the same;

the first electrode and the second electrode each have between about 4 and about 40 antennas; and

the apparatus is configured to provide relative motion between a substrate positioned on the substrate support and the electrode assembly.

9. An apparatus for processing a substrate, the apparatus comprising:

a substrate support, the substrate support comprising a surface configured to support a substrate thereon;

a heat source, the heat source configured to heat a substrate positioned on the surface of the substrate support;

an electrode assembly positioned opposite the surface of the substrate support, the electrode assembly comprising a first electrode and a second electrode, wherein:

the first electrode comprises between about 4 and about 40 antennas, wherein the one or more antennas of the first electrode project from a first support structure,

20

and wherein each antenna of the first electrode is substantially parallel to each other antenna of the first electrode;

the second electrode comprises between about 4 and about 40 antennas, wherein the one or more antennas of the second electrode project from a second support structure, and wherein each antenna of the second electrode is substantially parallel to each other antenna of the second electrode, and wherein each antenna of the first electrode is substantially parallel to each antenna of the second electrode;

at least one antenna of the first electrode and at least one antenna of the second electrode are interleaved;

the electrode assembly is configured to generate an electric field in a direction substantially parallel to the surface of the substrate support; and

a distance between each adjacent antenna of the first electrode is substantially the same, the distance between each adjacent antenna of the second electrode is substantially the same, and the distance between each adjacent antenna of the first electrode and each adjacent antenna of the second electrode is substantially the same; and

a magnetic field source, wherein the magnetic field source is configured to generate a magnetic field in a direction substantially perpendicular to the electric field and parallel to the surface of the substrate support.

10. The apparatus of claim 9, wherein the apparatus is configured to provide relative motion between a substrate positioned on the substrate support and the electrode assembly.

11. The apparatus of claim 9, wherein the substrate support and electrode assembly are positioned within a vacuum chamber.

12. The apparatus of claim 9, wherein the magnetic field source provides a magnetic field strength of between about 0.1 T and about 10 T above the surface of the substrate support.

* * * * *